

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	381	257/500.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:42
L2	134	257/502.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:43
L3	222	257/551.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:56
L4	838	257/409.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:57
L5	635	257/339.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:57
S1	46	(plurality adj impurity adj regions) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:56
S2	149	(plurality adj impurity) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:55
S3	277	(first adj impurity) and (second adj impurity) and (third adj impurity) and (fourth adj impurity) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:57

S4	7	(plurality adj dopant adj regions) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:57
S5	113	(plurality adj doped adj regions) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:56
S6	4	(plurality adj implanted adj regions) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:56
S7	25	(plurality adj diffused adj regions) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:56
S8	43	(plurality adj dopant) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:57
S9	223	(plurality adj doped) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:57
S10	32	(plurality adj implanted) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:57
S11	91	(plurality adj diffused) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 12:03

S12	83	(first adj dopant) and (second adj dopant) and (third adj dopant) and (fourth adj dopant) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:58
S13	140	(first adj doped) and (second adj doped) and (third adj doped) and (fourth adj doped) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:58
S14	7	(first adj implanted) and (second adj implanted) and (third adj implanted) and (fourth adj implanted) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:59
S15	19	(first adj implant) and (second adj implant) and (third adj implant) and (fourth adj implant) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 11:59
S16	20	(first adj diffused) and (second adj diffused) and (third adj diffused) and (fourth adj diffused) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 12:03
S17	152	(first adj diffusion) and (second adj diffusion) and (third adj diffusion) and (fourth adj diffusion) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 12:03
S18	192	(plurality adj diffusion) and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:21
S20	137	high adj breakdown adj voltage adj mosfet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:22

S21	414	high adj breakdown adj voltage adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:22
S22	145	high adj breakdown adj voltage adj mos adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:29
S23	8	high adj breakdown adj voltage adj metal adj oxide adj semiconductor adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:29
S24	19	high adj breakdown adj voltage adj metal adj oxide adj semiconductor adj field adj effect adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:30
S25	20	high adj breakdown adj voltage near (metal adj oxide adj semiconductor adj field adj effect adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:32
S26	48	(high adj breakdown adj voltage) with (metal adj oxide adj semiconductor adj field adj effect adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 13:33
S27	85	(high adj breakdown adj voltage) same (metal adj oxide adj semiconductor adj field adj effect adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:42